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Dual Retriggerable Monostable Multivibrators (with Clear)



ADE-205-438 (Z) 1st. Edition Sep. 2000

### **Description**

This multivibrator features both a negative, A, and a positive, B, transition triggered input, either of which can be used as an inhibit input. Also included is a clear input that when taken low resets the one shot. The HD74HC123A can be triggered on the positive transition of the clear while A is held low and B is held high.

The HD74HC123A is retriggerable. That is it may be triggered repeatedly while their outputs are generating a pulse and the pulse will be extended.

Pulse width stability over a wide range of temperature. The output pulse equation is simply:  $t_w = (Rext)$  (Cext).

#### **Features**

• High Speed Operation

• High Output Current: Fanout of 10 LSTTL Loads

Wide Operating Voltage: V<sub>CC</sub> = 2 to 6 V

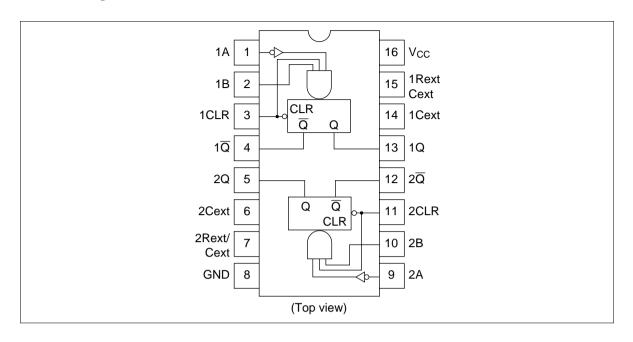
Low Input Current: 1 μA max
 Low Quiescent Supply Current

#### **Function Table**

| Inputs |   |   | Outputs |   |  |
|--------|---|---|---------|---|--|
| Clear  | Α | В | Q       | Q |  |
| L      | Х | Х | L       | Н |  |
| X      | Н | Χ | L       | Н |  |
| X      | Х | L | L       | Н |  |
| Н      | L |   | $\Box$  | T |  |
| Н      | _ | Н |         | T |  |
|        | L | Н | $\Box$  | T |  |

Note: External timing capacitance connects between Cext and Rext/Cext.

## **Pin Arrangement**



## **DC** Characteristics

|                |               | Sym-            | $\mathbf{v}_{cc}$ | Ta = | 25°C |      | Ta =<br>to +8 |      |      |  |                                 |
|----------------|---------------|-----------------|-------------------|------|------|------|---------------|------|------|--|---------------------------------|
| Item           |               | bol             | (V)               | Min  | Тур  | Max  | Min           | Max  | Unit | Test Conditions                          |                                 |
| Input voltage  |               | $V_{IH}$        | 2.0               | 1.5  | _    | _    | 1.5           | _    | V    |  |                                 |
|                |               |                 | 4.5               | 3.15 | _    | _    | 3.15          | _    | _    |  |                                 |
|                |               |                 | 6.0               | 4.2  | _    | _    | 4.2           | _    |      |  |                                 |
|                |               | $V_{IL}$        | 2.0               | _    | _    | 0.5  | _             | 0.5  | ٧    |  |                                 |
|                |               |                 | 4.5               | _    | _    | 1.35 | _             | 1.35 | _    |  |                                 |
|                |               |                 | 6.0               | _    | _    | 1.8  | _             | 1.8  |      |  |                                 |
| Output voltage |               | $V_{OH}$        | 2.0               | 1.9  | 2.0  | _    | 1.9           | _    | V    | $Vin = V_{IH} \text{ or } V_{IL}$        | $I_{OH} = -20 \mu A$            |
|                |               |                 | 4.5               | 4.4  | 4.5  | _    | 4.4           | _    | _    |  |                                 |
|                |               |                 | 6.0               | 5.9  | 6.0  | _    | 5.9           | _    |      |  |                                 |
|                |               |                 | 4.5               | 4.18 | _    | _    | 4.13          | _    | -    |  | $I_{OH} = -4 \text{ mA}$        |
|                |               |                 | 6.0               | 5.68 | _    | _    | 5.63          | _    | -    |  | $I_{OH} = -5.2 \text{ mA}$      |
|                |               | V <sub>OL</sub> | 2.0               | _    | 0.0  | 0.1  | _             | 0.1  | ٧    | Vin = V <sub>IH</sub> or V <sub>IL</sub> | I <sub>OL</sub> = 20 μA         |
|                |               |                 | 4.5               | _    | 0.0  | 0.1  | _             | 0.1  | =    |  |                                 |
|                |               |                 | 6.0               | _    | 0.0  | 0.1  | _             | 0.1  |      |  |                                 |
|                |               |                 | 4.5               | _    | _    | 0.26 | _             | 0.33 | -    |  | I <sub>OL</sub> = 4 mA          |
|                |               |                 | 6.0               | _    | _    | 0.26 | _             | 0.33 | -    |  | I <sub>OL</sub> = 5.2 mA        |
| Input current  |               | lin             | 6.0               | _    | _    | ±0.1 | _             | ±1.0 | μΑ   | Vin = V <sub>CC</sub> or GI              | ND                              |
| Quiescent      | Standby state | I <sub>cc</sub> | 6.0               | _    | _    | 130  | _             | 220  | μΑ   | Vin = V <sub>CC</sub> or                 | lout = 0 μA                     |
| supply current | Active state  |                 |                   | _    | _    | 130  | _             | 220  |      | GND                                      | Rext/Cext = 0.5 V <sub>CC</sub> |

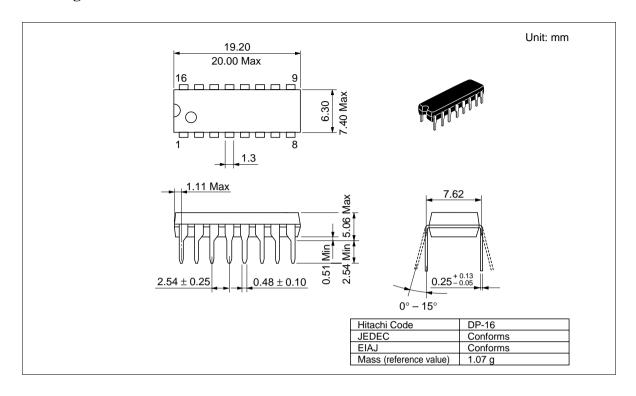
**AC Characteristics** ( $C_L = 50 \text{ pF}$ , Input  $t_r = t_f = 6 \text{ ns}$ )

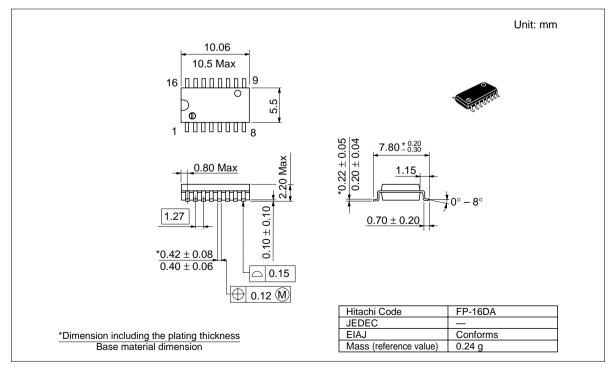
Ta = -40 to $Ta = 25^{\circ}C$  +85°C

| Item               | Symbol               | V <sub>cc</sub> (V) | Min | Тур | Max | Min | Max | Unit         | Test Conditions                         |
|--------------------|----------------------|---------------------|-----|-----|-----|-----|-----|--------------|---|
| Propagation delay  | t <sub>PLH</sub>     | 2.0                 | _   | _   | 210 | _   | 265 | ns           | A, B or Clear to Q                      |
| time               |                      | 4.5                 | _   | 22  | 42  | _   | 53  | =            |   |
|                    |                      | 6.0                 | _   | _   | 36  | _   | 45  | =            |   |
|                    | t <sub>PHL</sub>     | 2.0                 | _   | _   | 240 | _   | 300 | ns           | A, B or Clear to Q                      |
|                    |                      | 4.5                 | _   | 23  | 48  | _   | 60  | <del>-</del> |   |
|                    |                      | 6.0                 | _   | _   | 41  | _   | 51  | <del>-</del> |   |
|                    | t <sub>PHL</sub>     | 2.0                 | _   | _   | 170 | _   | 215 | ns           | Clear to Q                              |
|                    |                      | 4.5                 | _   | 18  | 34  | _   | 43  | <del>-</del> |   |
|                    |                      | 6.0                 | _   | _   | 29  | _   | 37  | _            |   |
|                    | t <sub>PLH</sub>     | 2.0                 | _   | _   | 180 | _   | 225 | ns           | Clear to Q                              |
|                    |                      | 4.5                 | _   | 16  | 36  | _   | 45  | _            |   |
|                    |                      | 6.0                 | _   | _   | 31  | _   | 38  | _            |   |
| Output rise time   | t <sub>TLH</sub>     | 2.0                 | _   | _   | 75  | _   | 95  | ns           |   |
|                    |                      | 4.5                 | _   | 5   | 15  | _   | 19  | _            |   |
|                    |                      | 6.0                 | _   | _   | 13  | _   | 16  | _            |   |
| Output fall time   | t <sub>THL</sub>     | 2.0                 | _   | _   | 75  | _   | 95  | ns           |   |
|                    |                      | 4.5                 | _   | 5   | 15  | _   | 19  | =            |   |
|                    |                      | 6.0                 | _   | _   | 13  | _   | 16  | _            |   |
| Pulse width        | t <sub>w</sub>       | 2.0                 | 150 | _   | _   | 190 | _   | ns           | A, B, Clear                             |
|                    |                      | 4.5                 | 30  | 6   | _   | 38  | _   | =            |   |
|                    |                      | 6.0                 | 26  | _   | _   | 33  | _   | _            |   |
| Minimum output     | t <sub>WQ(min)</sub> | 2.0                 | _   | 1.5 | _   | _   | _   | μs           | Cext = 28 pF Rext = $6 \text{ k}\Omega$ |
| pulse width        |                      | 4.5                 | _   | 450 | _   | _   | _   | ns           | Rext = $2 k\Omega$                      |
|                    |                      | 6.0                 | _   | 380 | _   | _   | _   |              |   |
| Output pulse width | t <sub>wq</sub>      | 4.5                 | _   | 1.0 | _   | _   |     | ms           | Cext = 0.1 $\mu$ F, Rext = 10 $k\Omega$ |
| Input capacitance  | Cin                  | _                   | _   | 5   | 10  | _   | 10  | pF           |   |

Caution in use: In order to prevent any malfunctions due to noise, connect a high-frequency performance capacitor between  $V_{cc}$  and GND, and keep the wiring between the External components and Cext, Rext/Cext pins as short as possible.

## **Package Dimensions**





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